

TC74HC85AP, TC74HC85AF, TC74HC85AFN

4 - BIT MAGNITUDE COMPARATOR

The TC74HC85A is a high speed CMOS 4 BIT MAGNITUDE COMPARATOR fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

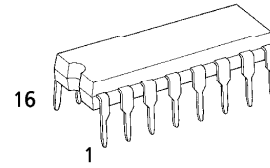
The TC74HC85A compares tow 4 - bit words applied to inputs A0 - A3 and B0 - B3 , and provides a high voltage level on one of three outputs : A>B, A<B, or A=B.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

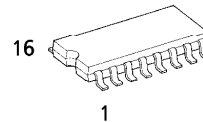
FEATURES :

- High Speed..... $t_{pd} = 22ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A$ (Max.) at $T_a = 25^{\circ}C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability..... 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA$ (Min.)
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range.... V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS85

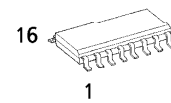
(Note) The JEDEC SOP (FN) is not available in Japan.



P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)

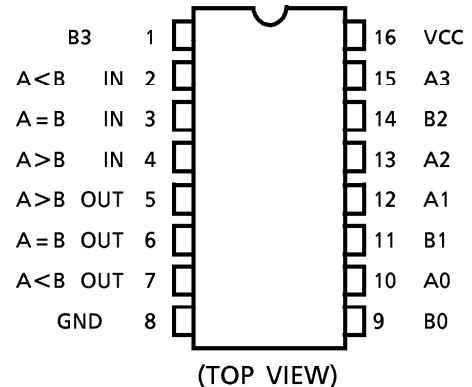


F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

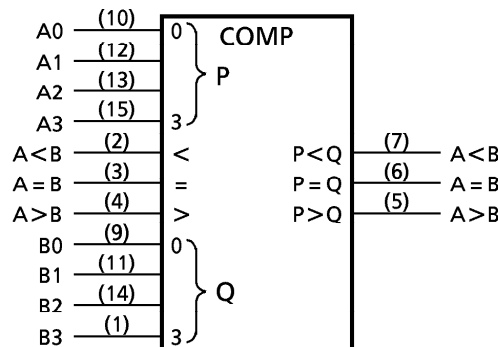


FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)

PIN ASSIGNMENT



IEC LOGIC SYMBOL



961001EBA2

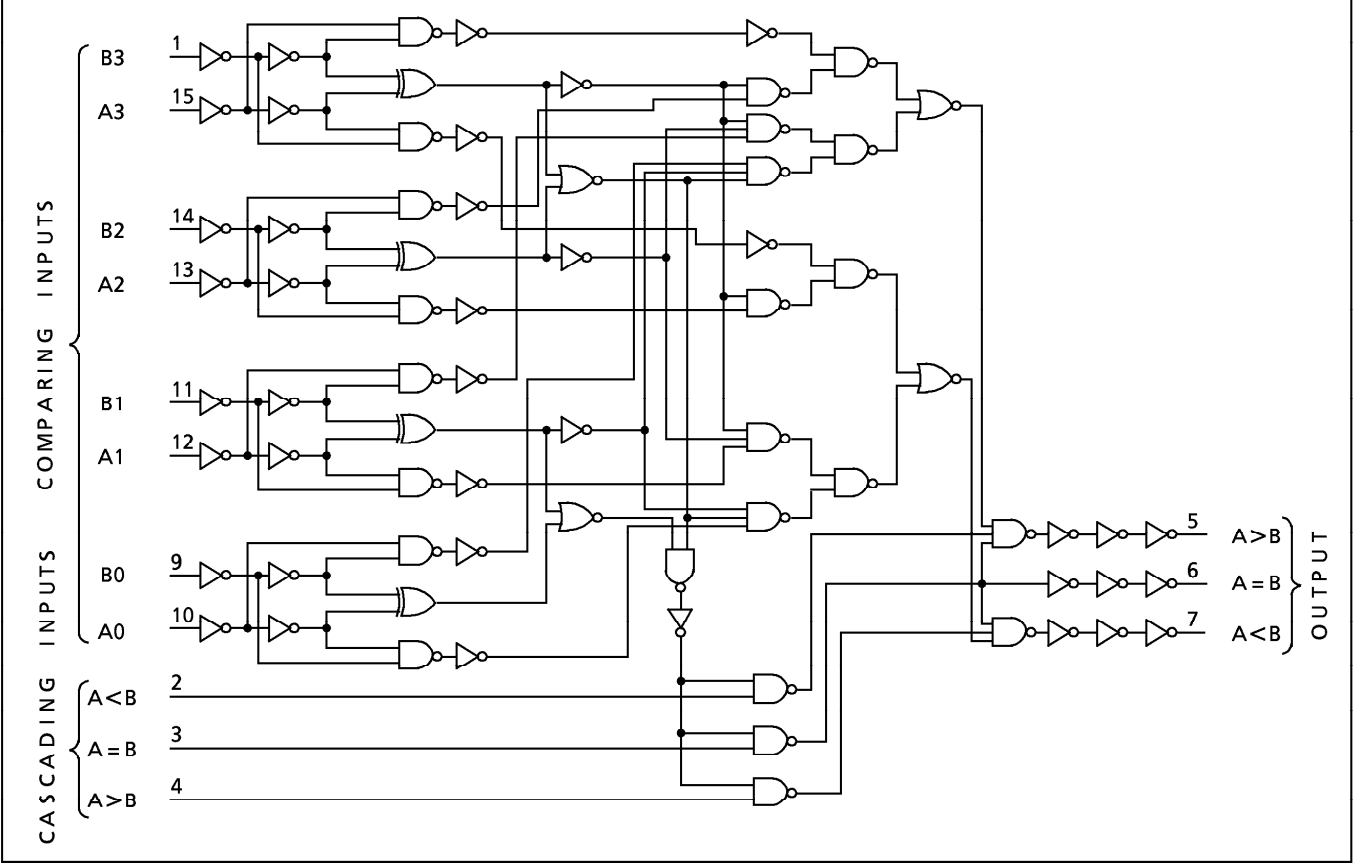
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TRUTH TABLE

COMPARING INPUT				CASCADING INPUT			OUTPUT		
				A>B	A<B	A=B	A>B	A<B	A=B
A3>B3	X	X	X	X	X	X	H	L	L
A3=B3	A2>B2	X	X	X	X	X	H	L	L
A3=B3	A2=B2	A1>B1	X	X	X	X	H	L	L
A3=B3	A2=B2	A1=B1	A0>B0	X	X	X	H	L	L
A3=B3 , A2=B2 , A1=B1 , A0=B0				L	L	L	H	H	L
				X	X	H	L	L	H
				L	H	L	L	H	L
				H	L	L	H	L	L
A3=B3	A2=B2	A1=B1	A0<B0	X	X	X	L	H	L
A3=B3	A2=B2	A1<B1	X	X	X	X	L	H	L
A3=B3	A2<B2	X	X	X	X	X	L	H	L
A3<B3	X	X	X	X	X	X	L	H	L

X : Don't Care

SYSTEM DIAGRAM



961001EBA2'

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2 \sim 6$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	t_r, t_f	$0 \sim 1000 (V_{CC} = 2.0\text{V})$ $0 \sim 500 (V_{CC} = 4.5\text{V})$ $0 \sim 400 (V_{CC} = 6.0\text{V})$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	V
			$I_{OH} = -4 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80	—	5.63	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	V
			$I_{OL} = 4 \text{ mA}$	4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	
			$I_{OL} = 5.2 \text{ mA}$	6.0	—	0.18	0.26	0.33 0.33	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or } \text{GND}$	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or } \text{GND}$	6.0	—	—	4.0	—	40.0	

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time (A , B — OUT)	t_{PLH} t_{PHL}		—	22	34	
Propagation Delay Time (CASCADE — OUT)	t_{PLH} t_{PHL}		—	10	18	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

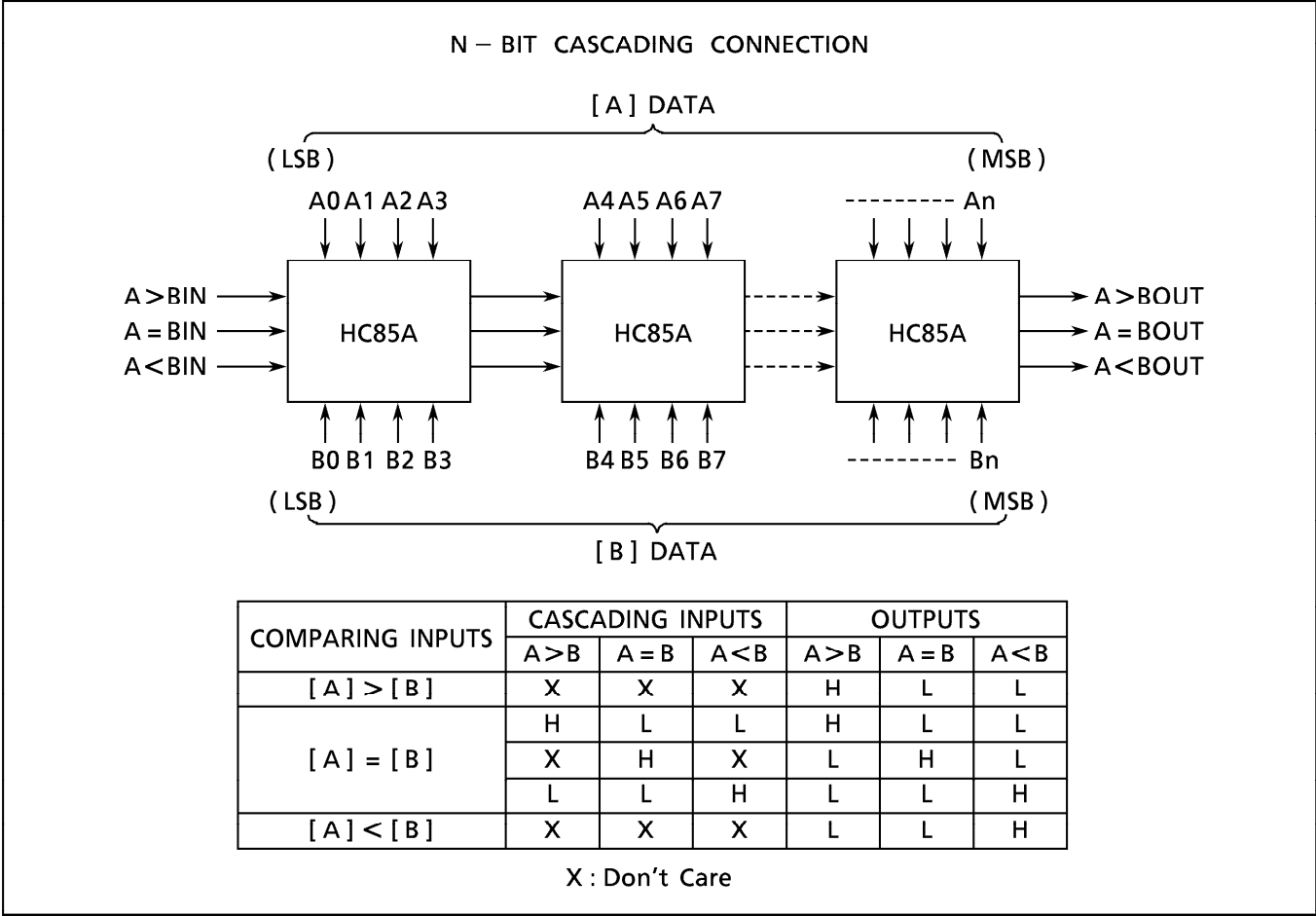
PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Output Transition Time	t _{TLH} t _{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time (A , B—OUT)	t _{pLH} t _{pHL}		2.0	—	90	195	—	245	
			4.5	—	26	39	—	49	
			6.0	—	22	33	—	42	
Propagation Delay Time (CASCADE—OUT)	t _{pLH} t _{pHL}		2.0	—	40	110	—	140	
			4.5	—	13	22	—	28	
			6.0	—	11	19	—	24	
Input Capacitance	C _{IN}		—	5	10	—	10	pF	
Power Dissipation Capacitance	C _{PD} (1)		—	25	—	—	—		

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

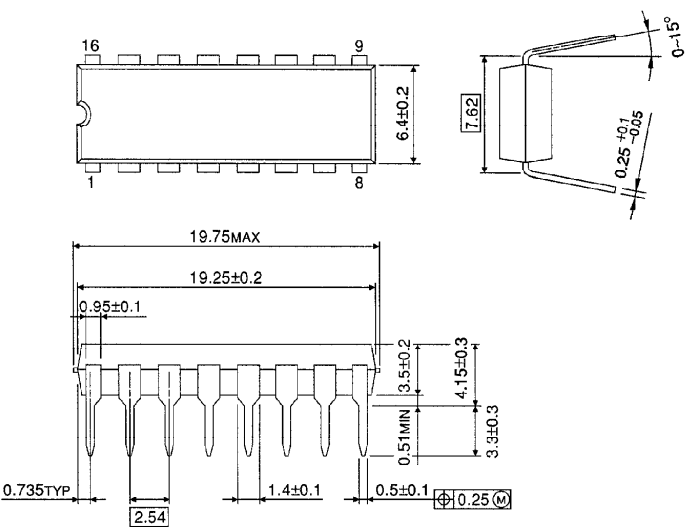
$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

TYPICAL APPLICATION



DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

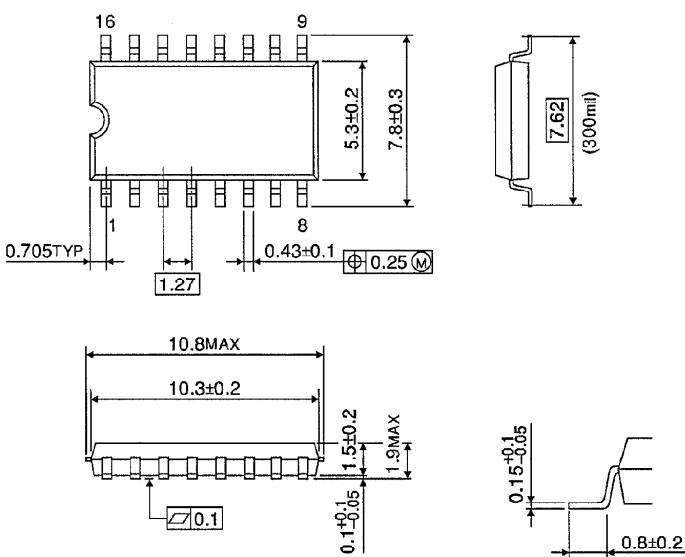
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

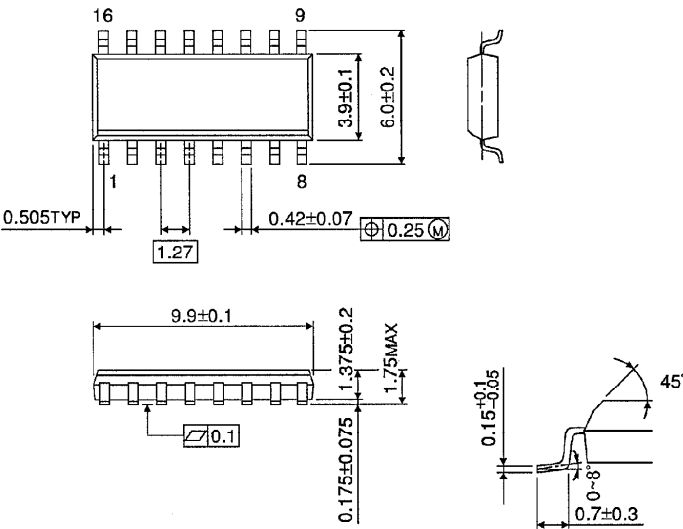


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)